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BS108

Small Signal MOSFET 250 mAmps, 200 Volts, Logic Level

N-Channel TO-92

This MOSFET is designed for high voltage, high speed switching applications such as line drivers, relay drivers, CMOS logic, microprocessor or TTL to high voltage interface and high voltage display drivers.

Features

- Low Drive Requirement, $V_{GS} = 3.0 \text{ V max}$
- Inherent Current Sharing Capability Permits Easy Paralleling of many Devices
- AEC Qualified
- PPAP Capable
- This is a Pb-Free Device*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	200	Vdc
Gate-Source Voltage	V_{GS}	± 20	Vdc
Drain Current Continuous (Note 1) Pulsed (Note 2)	I_D I_{DM}	250 500	mAdc
Total Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above $T_A = 25^\circ\text{C}$	P_D	350 6.4	mW mW/ $^\circ\text{C}$
Operating and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. The Power Dissipation of the package may result in a lower continuous drain current.
2. Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2.0\%$.



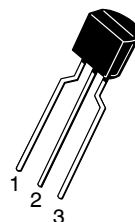
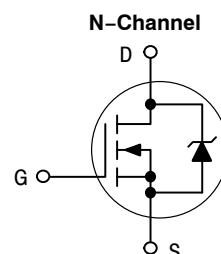
ON Semiconductor®

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250 mAmps

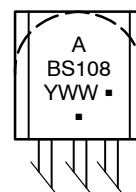
200 VOLTS

$R_{DS(on)} = 8 \Omega$



TO-92
CASE 29-11
STYLE 30

MARKING DIAGRAM



BS108 = Device Code

A = Assembly Location

Y = Year

WW = Work Week

▪ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping
BS108ZL1G	TO-92 (Pb-Free)	2000/Ammo Pack

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Drain-Source Breakdown Voltage ($V_{GS} = 0$, $I_D = 10\ \mu\text{A}$)	$V_{(BR)DS}$	200	–	–	Vdc
Zero Gate Voltage Drain Current ($V_{DSS} = 130\ \text{Vdc}$, $V_{GS} = 0$)	I_{DSS}	–	–	30	nAdc
Gate-Body Leakage Current ($V_{GS} = 15\ \text{Vdc}$, $V_{DS} = 0$)	I_{GSSF}	–	–	10	nAdc
ON CHARACTERISTICS (Note 3)					
Gate Threshold Voltage ($I_D = 1.0\ \text{mA}$, $V_{DS} = V_{GS}$)	$V_{GS(th)}$	0.5	–	1.5	Vdc
Static Drain-to-Source On-Resistance ($V_{GS} = 2.0\ \text{Vdc}$, $I_D = 50\ \text{mA}$) ($V_{GS} = 2.8\ \text{Vdc}$, $I_D = 100\ \text{mA}$)	$r_{DS(on)}$	– –	– –	10 8.0	Ω
Drain Cutoff Current ($V_{GS} = 0.2\ \text{V}$, $V_{DS} = 70\ \text{V}$)	I_{DSX}	–	–	25	μA
Forward Transconductance ($I_D = 120\ \text{mA}$, $V_{DS} = 20\ \text{V}$)	g_{FS}	–	0.33	–	Mhos
DYNAMIC CHARACTERISTICS					
Input Capacitance ($V_{DS} = 25\ \text{V}$, $V_{GS} = 0$, $f = 1.0\ \text{MHz}$)	C_{iss}	–	–	150	pF
Output Capacitance ($V_{DS} = 25\ \text{V}$, $V_{GS} = 0$, $f = 1.0\ \text{MHz}$)	C_{oss}	–	–	30	pF
Reverse Transfer Capacitance ($V_{DS} = 25\ \text{V}$, $V_{GS} = 0$, $f = 1.0\ \text{MHz}$)	C_{rss}	–	–	10	pF
SWITCHING CHARACTERISTICS					
Turn-On Time (See Figure 1)	$t_{d(on)}$	–	–	15	ns
Turn-Off Time (See Figure 1)	$t_{d(off)}$	–	–	15	ns

3. Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle = 2.0%.

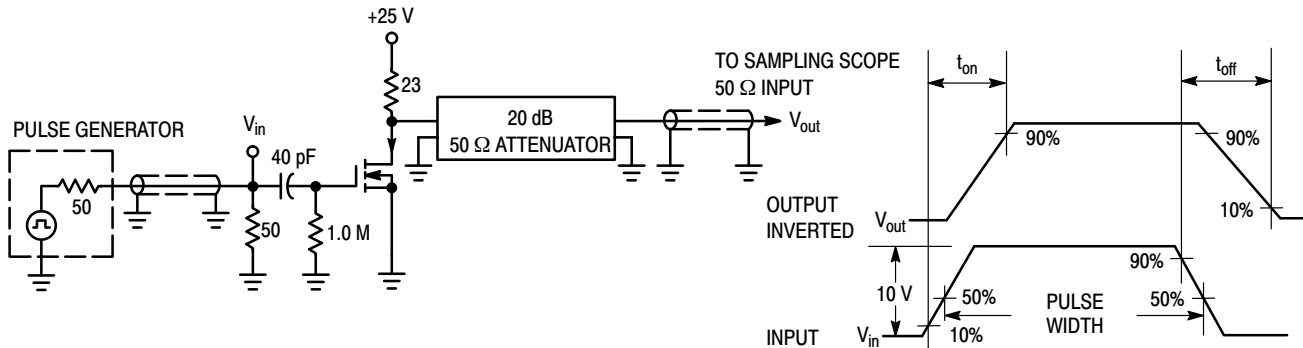
RESISTIVE SWITCHING

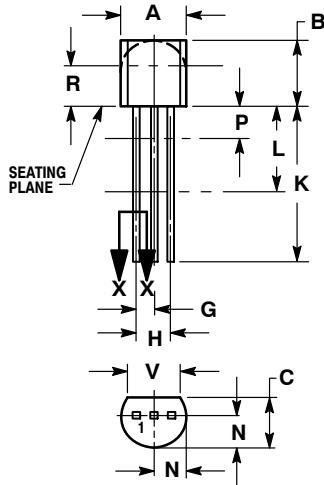
Figure 1. Switching Test Circuit

Figure 2. Switching Waveforms

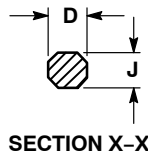
BS108

PACKAGE DIMENSIONS

TO-92 (TO-226)
CASE 29-11
ISSUE AM



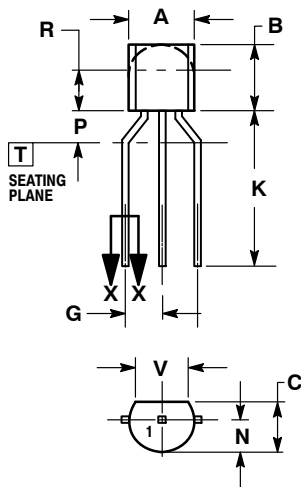
STRAIGHT LEAD
BULK PACK



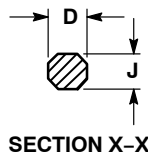
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.115	---	2.93	---
V	0.135	---	3.43	---



BENT LEAD
TAPE & REEL
AMMO PACK



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	MILLIMETERS	
	MIN	MAX
A	4.45	5.20
B	4.32	5.33
C	3.18	4.19
D	0.40	0.54
G	2.40	2.80
J	0.39	0.50
K	12.70	---
N	2.04	2.66
P	1.50	4.00
R	2.93	---
V	3.43	---

STYLE 30:

1. DRAIN
2. GATE
3. SOURCE

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